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Title: A CMOS Magnetic Hall Sensor Using a Switched Biasing Amplifier

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Abstract:A compact CMOS magnetic Hall sensor that includes both a Hall plate and readout circuit is proposed. In order to achieve a low-noise and low-power operation, the sensor employs a switched biasing amplifier with a chopper. The prototype has been implemented and fabricated in a high-voltage 0.18 CMOS process and occupies 0.624 mm². Owing to the switched biasing amplifier, the input-referred noise is reduced from 41 μT√Hz to 25 μT/ √Hz. The entire sensor consumes 4.5 mW with a 3.3 V supply voltage.

Number of references:5

Inspec controlled terms:amplifiers - choppers (circuits) - CMOS integrated circuits - Hall effect transducers - low-power electronics - magnetic sensors

Uncontrolled terms:switched biasing amplifier - compact CMOS magnetic Hall sensor - Hall plate - readout circuit - low-noise operation - low-power operation - chopper - high-voltage CMOS processing - input-referred noise reduction - size 0.18 mum - power 4.5 mW - voltage 3.3 V

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Numerical data indexing:size 1.8E-07 m;power 4.5E-03 W;voltage 3.3E+00 V

Treatment: Practical (PRA); Experimental (EXP)

Discipline:Electrical/Electronic engineering (B)

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